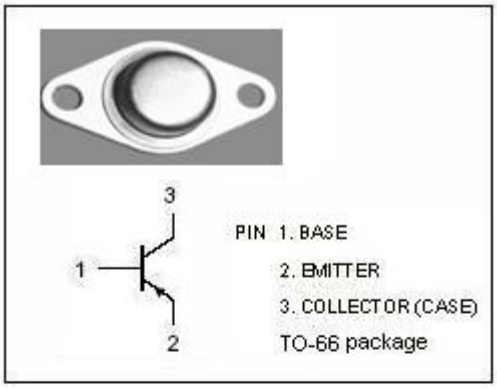
isc Silicon PNP Power Transistors — 2SB551

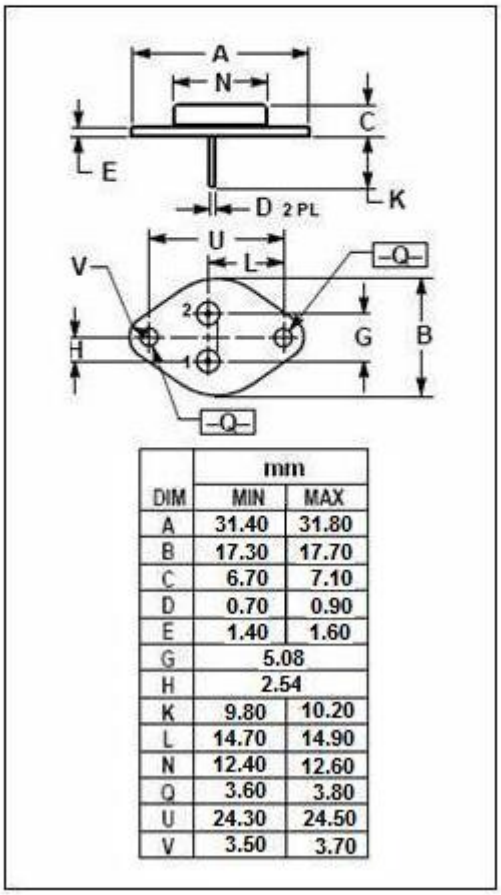
DESCRIPTION

- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -1.2V(Typ.)@I_C= -2A
- High Power Dissipation-
  : P_C= 25W(Max)@T_C=55℃
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for low frequency power amplifier applications.



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_C= 25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-45~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; R_{BE}= ∞	-50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -5mA; I_E= 0	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -5mA; I_C= 0	-4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -1A; V_{CE}= -4V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -20V; I_E= 0			-0.1	mA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -4V	35		200	
h_{FE-2}	DC Current Gain	I_C= -0.1A; V_{CE}= -4V	35			
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -4V	15			MHz

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200